

3DA101, 3DA102**NPN Silicon High Frequency High Power Transistor****Features:**

1. Excellent second breakdown capacity. Good characteristic frequency.
2. Amplification factor of small current is great. Good voltage resistance.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for analog computer power output, amplification of high frequency,middle frequency and low frequency, switching circuit.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications	
			3DA101	3DA102
Total Dissipation (Tc≤75°C)	P _{tot}	W	7.5	
Max. Collector Current	I _{CM}	A	1.0	
Junction Temperature	T _{jm}	°C	175	
Storage Temperature	T _{stg}	°C	-55~+175	
C-E Breakdown Voltage	V _{(BR)CEO}	V	30~70 (I _c =2mA)	30~50 (I _c =2mA)
E-B Breakdown Voltage	V _{(BR)EBO}	V	≥5 (I _E =2mA)	
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	1.0	1.5
			I _c =0.5A, I _B =0.1A	
Collector-Base Leakage Current	I _{CBO}	mA	-	
C-E Leakage Current	I _{CEO}	mA	1.0	2.0
			V _{CE} =20V	
Emitter-Base Leakage Current	I _{EBO}	mA	2.0 (V _{EB} =5V)	
DC Current Gain	h _{FE}		≥10	
			V _{CE} =5V, I _c =0.3A	
Transition frequency	f _T	MHz	≥50	≥70
			V _{CE} =10V, I _c =0.2A, f _o =10 MHz	

Outline and Dimensions: